

**TO - 92 BIPOLAR TRANSISTORS
TRANSISTOR(NPN)**

FEATURES

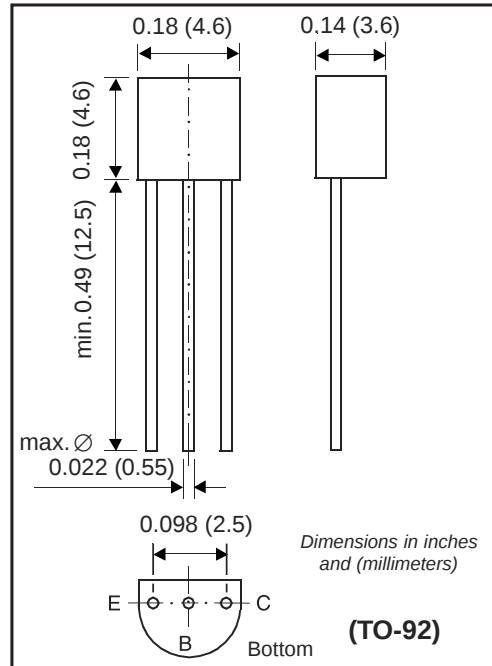
- * Power dissipation
P_{CM}: 625mW(T_{amb}=25°C)
- * Collector current
I_{CM}: 0.6 A
- * Collector-base voltage
V_{(BR)CBO}: 75 V
- * Operating and storage junction temperature range
T_J, T_{stg}: -55°C to +150°C

MECHANICAL DATA

- * Case: Molded plastic
- * Epoxy: UL 94V-O rate flame retardant
- * Lead: MIL-STD-202E method 208C guaranteed
- * Mounting position: Any
- * Weight: 0.008 gram

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.
Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%.



MAXIMUM RATINGS (@ T_A = 25°C unless otherwise noted)

RATINGS	SYMBOL	VALUE	UNITS
Max. Steady State Power Dissipation ⁽¹⁾ @T _A =25°C Derate above 25°C	P _D	625	mW
Max. Operating Temperature Range	T _J	150	°C
Storage Temperature Range	T _{STG}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (@ T_A = 25°C unless otherwise noted)

CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNITS
Thermal Resistance Junction to Ambient	R _{θJA}	-	-	200	°C/W

Notes : 1. Alumina=0.4*0.3*0.024in.99.5% alumina
2. "Fully ROHS Compliant", "100% Sn plating (Pb-free)".

2011-2

ELECTRICAL CHARACTERISTICS (@TA=25°C unless otherwise noted)

Chataacteristic	Symbol	Min	Max	Unit
-----------------	--------	-----	-----	------

OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ($I_C = 10\text{mA}$, $I_B = 0$)	$V_{(BR)CEO}$	40	-	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\mu\text{A}$, $I_E = 0$)	$V_{(BR)CBO}$	75	-	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\mu\text{A}$, $I_C = 0$)	$V_{(BR)EBO}$	6.0	-	Vdc
Collector Cutoff Current ($V_{CE} = 60\text{Vdc}$, $V_{EB(off)} = 3.0\text{Vdc}$)	I_{CEX}	-	0.01	μA
Collector Cutoff Current ($V_{CB} = 60\text{Vdc}$, $I_E = 0$)	I_{CBO}	-	0.01	μA
($V_{CB} = 60\text{Vdc}$, $I_E = 0$, $T_A = 150^\circ\text{C}$)		-	10	μA
Emitter Cutoff Current ($V_{EB} = 3.0\text{Vdc}$, $I_C = 0$)	I_{EBO}	-	0.01	μA
Base Cutoff Current ($V_{CE} = 60\text{Vdc}$, $V_{EB(off)} = 3.0\text{Vdc}$)	I_{BL}	-	20	nA

ON CHARACTERISTICS

DC Current Gain ($I_C = 10\text{mA}$, $V_{CE} = 10\text{Vdc}$, $T_A = -55^\circ\text{C}$)	hFE	35	-	-
($I_C = 500\text{mA}$, $V_{CE} = 10\text{Vdc}$) (1)		40	-	
Collector-Emitter Saturation Voltage (1) ($I_C = 150\text{mA}$, $I_B = 15\text{mA}$)	$V_{CE(sat)}$	-	0.3	Vdc
($I_C = 500\text{mA}$, $I_B = 50\text{mA}$)		-	1.0	
Base-Emitter Saturation Voltage (1) ($I_C = 150\text{mA}$, $I_B = 15\text{mA}$)	$V_{BE(sat)}$	0.6	1.2	Vdc
($I_C = 500\text{mA}$, $I_B = 50\text{mA}$)		-	2.0	

SMALL-SIGNAL CHARACTERISTICS

Current-Gain-Bandwidth Product (2) ($I_C = 20\text{mA}$, $V_{CE} = 20\text{Vdc}$, $f = 100\text{MHz}$)	f_T	300	-	MHz
Input Capacitance ($V_{EB} = 0.5\text{Vdc}$, $I_C = 0$, $f = 1.0\text{MHz}$)	C_{ibo}	-	25	pF
Input Impedance ($I_C = 1.0\text{mA}$, $V_{CE} = 10\text{Vdc}$, $f = 1.0\text{kHz}$)	h_{ie}	2.0	8.0	kohms
($I_C = 10\text{mA}$, $V_{CE} = 10\text{Vdc}$, $f = 1.0\text{kHz}$)		0.25	1.25	
Voltage Feedback Ratio ($I_C = 1.0\text{mA}$, $V_{CE} = 10\text{Vdc}$, $f = 1.0\text{kHz}$)	h_{re}	-	8.0	$\times 10^{-4}$
($I_C = 10\text{mA}$, $V_{CE} = 10\text{Vdc}$, $f = 1.0\text{kHz}$)		-	4.0	
Small-Signal Current Gain ($I_C = 1.0\text{mA}$, $V_{CE} = 10\text{Vdc}$, $f = 1.0\text{kHz}$)	h_{fe}	50	300	-
($I_C = 10\text{mA}$, $V_{CE} = 10\text{Vdc}$, $f = 1.0\text{kHz}$)		75	375	
Output Admittance ($I_C = 1.0\text{mA}$, $V_{CE} = 10\text{Vdc}$, $f = 1.0\text{kHz}$)	h_{oe}	5.0	35	μmhos
($I_C = 10\text{mA}$, $V_{CE} = 10\text{Vdc}$, $f = 1.0\text{kHz}$)		25	200	
Collector Base Time Constant ($I_E = 20\text{mA}$, $V_{CB} = 20\text{Vdc}$, $f = 31.8\text{MHz}$)	$\tau_{b,Cc}$	-	150	ps
Noise Figure ($I_C = 100\mu\text{A}$, $V_{CE} = 10\text{Vdc}$, $R_S = 1.0\text{kohms}$, $f = 1.0\text{kHz}$)	NF	-	4.0	dB

SWITCHING CHARACTERISTICS

Delay Time	$(V_{CC} = 30\text{Vdc}$, $V_{BE(off)} = -0.5\text{Vdc}$, $I_C = 150\text{mA}$, $I_{B1} = 15\text{mA}$)	t_d	-	10	ns
Rise Time		t_r	-	25	
Storage Time	$(V_{CC} = 30\text{Vdc}$, $I_C = 150\text{mA}$, $I_{B1} = I_{B2} = 15\text{mA}$)	t_s	-	225	ns
Fall Time		t_f	-	60	

NOTES : 1. Pulse Test: Pulse Width≤300ms,Duty Cycle≤2.0%
2. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity

RATING AND CHARACTERISTICS CURVES (PN2222A)

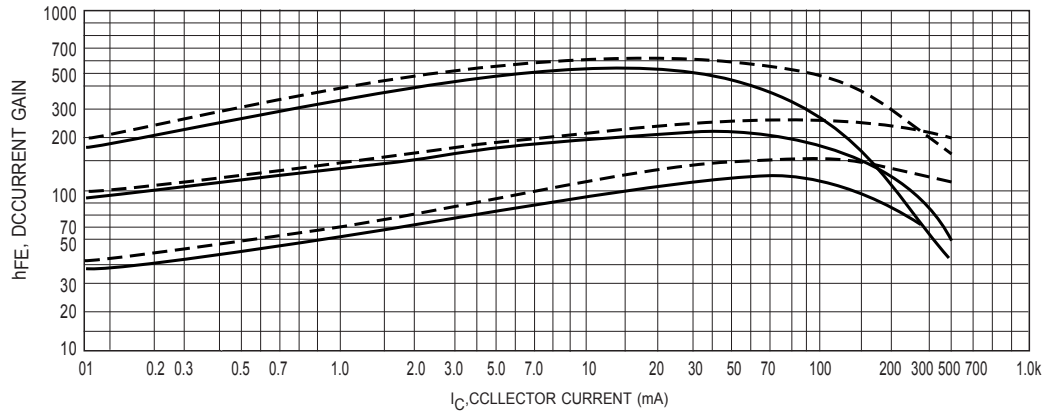


Figure 1. DC Current Gain

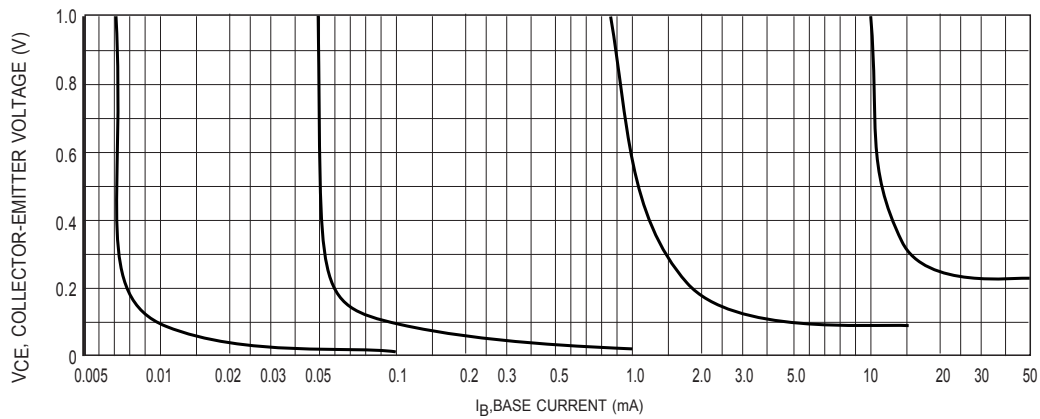


Figure 2. Collector Saturation Region

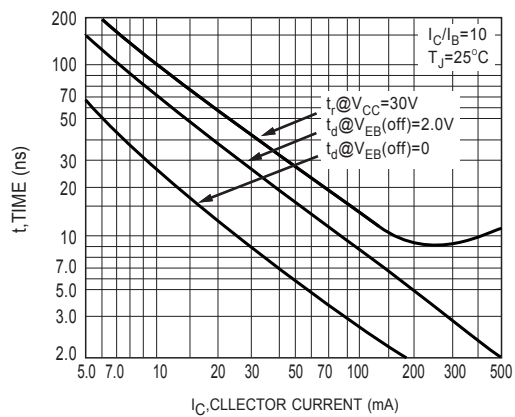


Figure 3. Turn-On Time

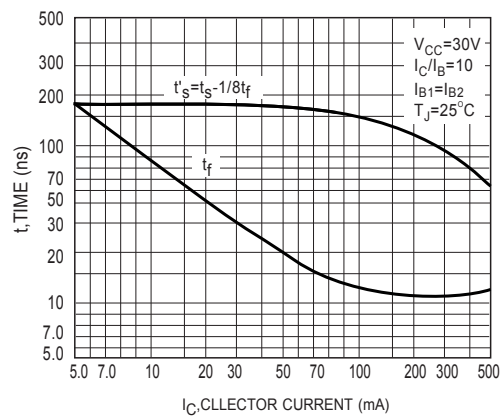


Figure 4. Turn-Off Time

RATING AND CHARACTERISTICS CURVES (PN2222A)

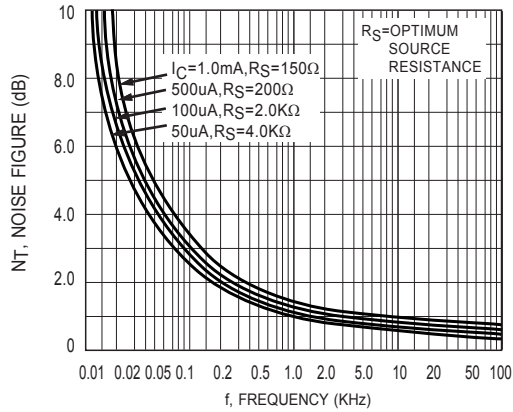


Figure 5.Frequency Effects

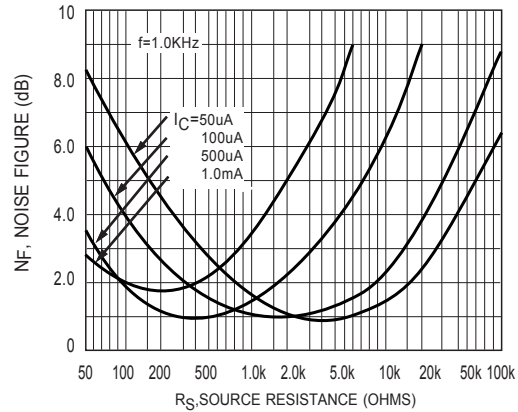


Figure 6.Source Resistance Effects

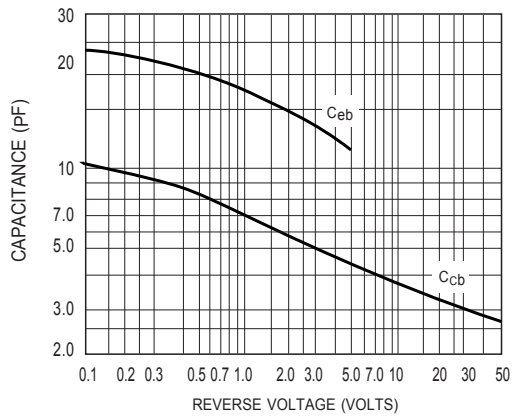


Figure 7.Capacitances

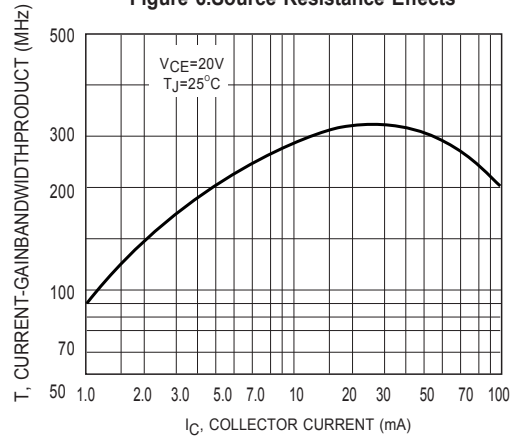


Figure 8.Currunt-Gain Bandwidth Product

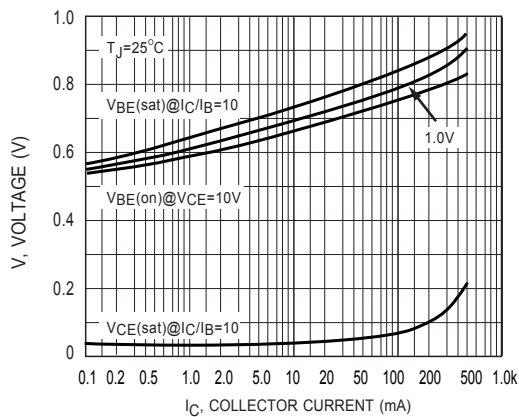


Figure 9."On" Voltages

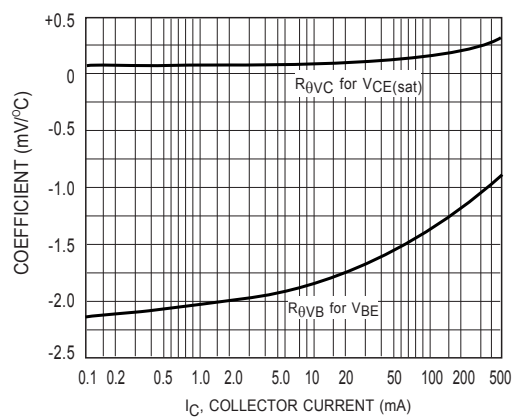


Figure 10.Temperature Coefficients

DISCLAIMER NOTICE

Rectron Inc reserves the right to make changes without notice to any product specification herein, to make corrections, modifications, enhancements or other changes. Rectron Inc or anyone on its behalf assumes no responsibility or liability for any errors or inaccuracies. Data sheet specifications and its information contained are intended to provide a product description only. "Typical" parameters which may be included on RECTRON data sheets and/ or specifications can and do vary in different applications and actual performance may vary over time. Rectron Inc does not assume any liability arising out of the application or use of any product or circuit.

Rectron products are not designed, intended or authorized for use in medical, life-saving implant or other applications intended for life-sustaining or other related applications where a failure or malfunction of component or circuitry may directly or indirectly cause injury or threaten a life without expressed written approval of Rectron Inc. Customers using or selling Rectron components for use in such applications do so at their own risk and shall agree to fully indemnify Rectron Inc and its subsidiaries harmless against all claims, damages and expenditures.

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9